

citric acid acting as a surface passivation agent, wherein

(C) ^{end}
said conditioning solution is substantially non-aqueous and configured to minimize the removal of metal lines from exposed surfaces of said semiconductor substrate while said residues are being removed from said semiconductor substrate.

150. (Twice Amended) A conditioning solution for use in removing residues remaining on a semiconductor substrate after a dry etch process, said conditioning solution comprising:

hydrofluoric acid;

hydrochloric acid;

propylene glycol; and

COP₄
citric acid acting as a surface passivation agent, wherein

CD₄
said conditioning solution is substantially non-aqueous and configured to minimize the removal of metal lines from exposed surfaces of said semiconductor substrate while said residues are being removed from said semiconductor substrate.

158. (Twice Amended) A conditioning solution for use in removing residues remaining on a semiconductor substrate after a dry etch process consisting essentially of a fluorine source, a complementary acid, a non-aqueous solvent and a surface passivation agent, wherein

CD₅
said conditioning solution is substantially non-aqueous and configured to minimize the removal of metal lines from exposed surfaces of said semiconductor substrate while said residues are being removed from said semiconductor substrate.